

Docket No. 264197US0PCT

JC02 Rec'd PCT/PTO 21 MAR 2005
MAR 21 2005
PATENT & TRADEMARK OFFICE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Shinsuke SADAMITSU, et al.

SERIAL NO: 10/519,837

GAU:

FILED: January 11, 2005

EXAMINER:

FOR: HIGH-RESISTANCE SILICON WAFER AND ITS MANUFACTURING METHOD

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references cited in the International Search Report and listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s), published application(s) or issued patent(s) which may be related to the present application. In accordance with the waiver of 37 CFR 1.98 dated September 21, 2004, copies of the cited pending applications are not provided. Cited published and/or issued patents, if any, are listed on the attached PTO form 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

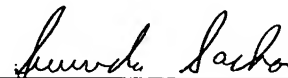
- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 264197US0PCT		SERIAL NO. 10/519,837	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Shinsuke SADAMITSU, et al.			
				FILING DATE January 11, 2005		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO	1087041	03/28/01	EP		NO	
	AP	5-144827	06/11/93	JP		NO	
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AW	BABICH, V.M. et al., 'Generation of thermal donors as a result of one- and two-step annealing of silicon crystals with large and small carbon concentrations', Semiconductors, Vol. 30, No. 5, pages 417 to 419, May 1996.					
	AX	KODATE, Junichi et al., Suppression of Substrate Crosstalk in Mixed-Signal Complementary MOS Circuits Using High-Resistivity SIMOX (Separation by Implanted OXYgen) Wafers, Japanese Journal of Applied Physics, Part 1, Vol.39, No.4B, pages 2256 to 2260, April 2000.					
	AY	WIJARANAKULA, W. et al., 'A Formation of Crystal Defects in Carbon-Doped Czochralski-Grown Silicon after a Three-Step Internal Gettering Anneal', Journal of Electrochemical Society, Vol.138, No.7, pages 2153 to 2159, July 1991.					
	AZ	GAWORZEWSKI P. et al., "Oxygen-Related Donors Formed at 600°C in Silicon in Dependence on Oxygen and Carbon Content", Phys.Stat.Sol. (a), Vol.77, No.2, pages 571 to 582, 1983				<input type="checkbox"/> Additional References sheet(s) attached	
Examiner							
Date Considered							
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							